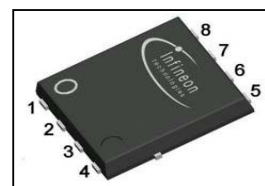
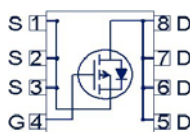


**OptiMOS<sup>®</sup>-P Power-Transistor**
**Features**

- P-Channel
- Enhancement mode
- Logic level
- 150°C operating temperature
- Avalanche rated
- V<sub>gs</sub>=25V, specially suited for notebook applications


**Product Summary**

$V_{DS}$	-30	V
$R_{DS(on),max}$	8	mΩ
$I_D$	-30	A

**PG-TDSON-8**


Type	Package	Marking	Lead free	Packing
BSC080P03LS G	PG-TDSON-8	080P03LS	Yes	Dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ °C}$	-30	A
		$T_C=70\text{ °C}$	-30	
		$T_A=25\text{ °C}^{(1)}$	-16	
Pulsed drain current	$I_{D,pulse}$	$T_C=25\text{ °C}^{(2)}$	-120	
Avalanche energy, single pulse	$E_{AS}$	$I_D=-30\text{ A}, R_{GS}=25\text{ }\Omega$	248	mJ
Gate source voltage	$V_{GS}$		$\pm 25$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	89	W
		$T_A=25\text{ °C}^{(1)}$	2.8	
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150	°C
ESD class		JESD22-C101-HBM	1C (1kV-2kV)	
Soldering temperature			260 °C	
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	1.4	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	6 cm <sup>2</sup> cooling area <sup>1)</sup>	-	-	50	

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=-250\text{ }\mu\text{A}$	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\text{ }\mu\text{A}$	-2.2	-1.5	-1	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	-0.1	-1	$\mu\text{A}$
		$V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$	-	-10	-100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=-25\text{ V}, V_{DS}=0\text{ V}$	-	-10	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10\text{ V}, I_D=-30\text{ A}$	-	6.1	8.0	m $\Omega$
Gate resistance	$R_G$		-	4	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=-30\text{ A}$	30	60	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

<sup>2)</sup> See Figure 3.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=-15\text{ V},$ $f=1\text{ MHz}$	-	4620	6140	pF
Output capacitance	$C_{oss}$		-	1430	1900	
Reverse transfer capacitance	$C_{rss}$		-	1200	1800	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V}, V_{GS}=-10\text{ V}, I_D=-30\text{ A},$ $R_G=6\ \Omega$	-	13.5	20.3	ns
Rise time	$t_r$		-	87.0	130.5	
Turn-off delay time	$t_{d(off)}$		-	79.0	118.5	
Fall time	$t_f$		-	108.0	162.0	

**Gate Charge Characteristics<sup>3)</sup>**

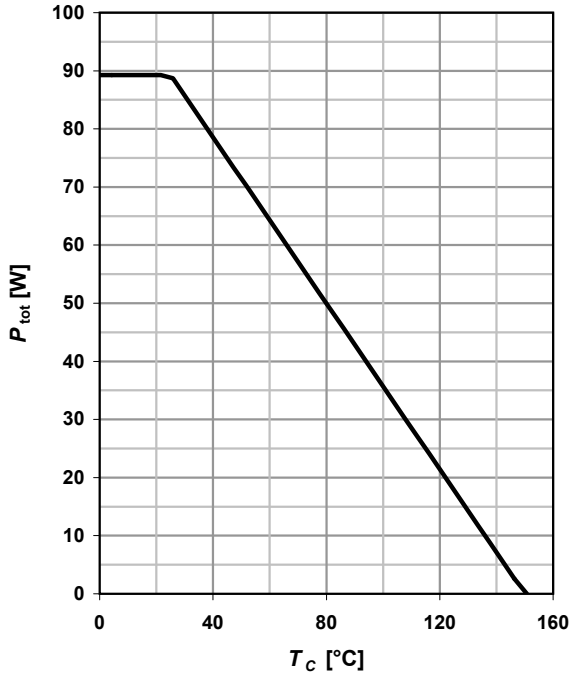
Gate to source charge	$Q_{gs}$	$V_{DD}=-24\text{ V}, I_D=30\text{ A},$ $V_{GS}=0\text{ to }-10\text{ V}$	-	-12.7	-16.8	nC
Gate charge at threshold	$Q_{g(th)}$		-	-7.1	-9.5	
Gate to drain charge	$Q_{gd}$		-	-34.3	-51.4	
Switching charge	$Q_{sw}$		-	-39.8	-58.8	
Gate charge total	$Q_g$		-	-92.0	-122.4	
Gate plateau voltage	$V_{plateau}$		-	-2.8	-	V
Output charge	$Q_{oss}$	$V_{DD}=-15\text{ V}, V_{GS}=0\text{ V}$	-	25.6	34.0	

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	30.0	A
Diode pulse current	$I_{S,pulse}$		-	-	-120	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-30\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	-0.9	-1.2	V
Reverse recovery time	$t_{rr}$	$V_R=15\text{ V}, I_F= I_S ,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	35	44	ns
Reverse recovery charge	$Q_{rr}$		-	28.0	-	nC

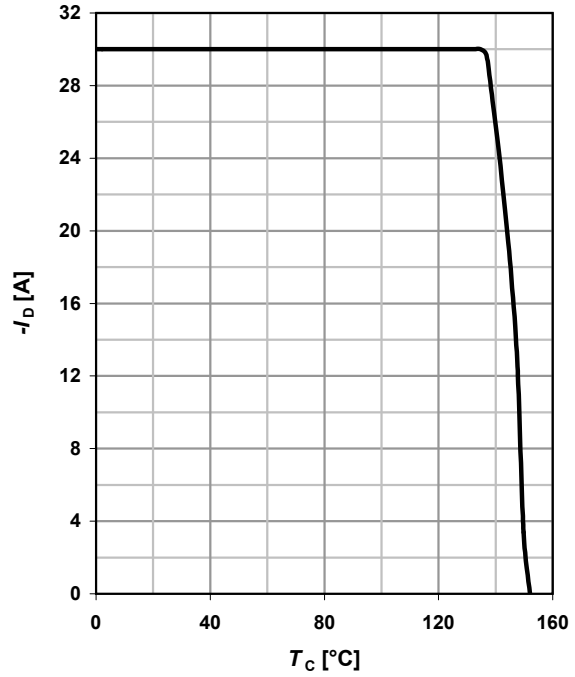
**1 Power dissipation**

$P_{tot}=f(T_C); t_p \leq 10 \text{ s}$



**2 Drain current**

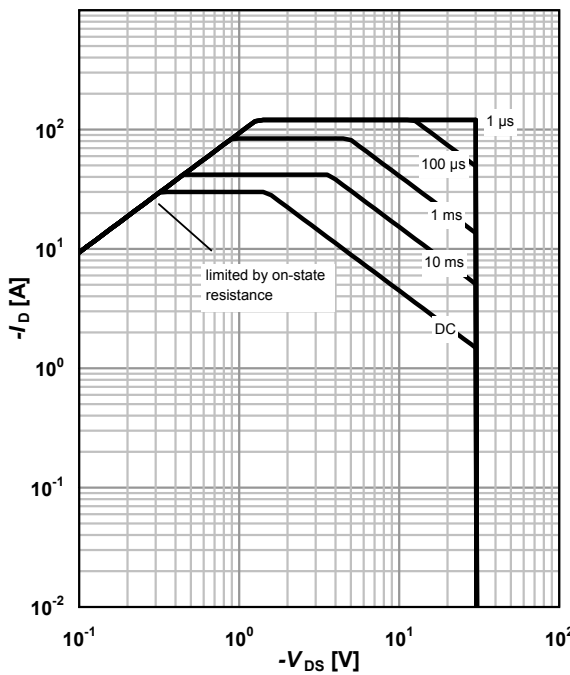
$I_D=f(T_C); |V_{GS}| \geq 10 \text{ V}; t_p \leq 10 \text{ s}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25 \text{ }^\circ\text{C}^1; D=0$

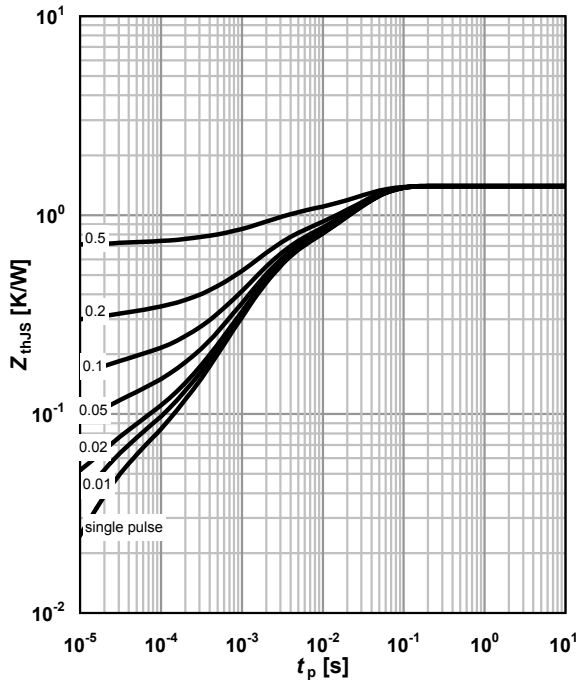
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJS}=f(t_p)$

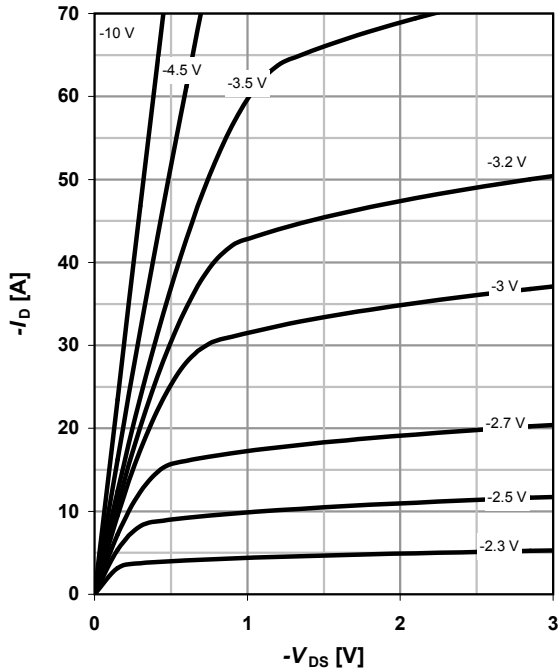
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

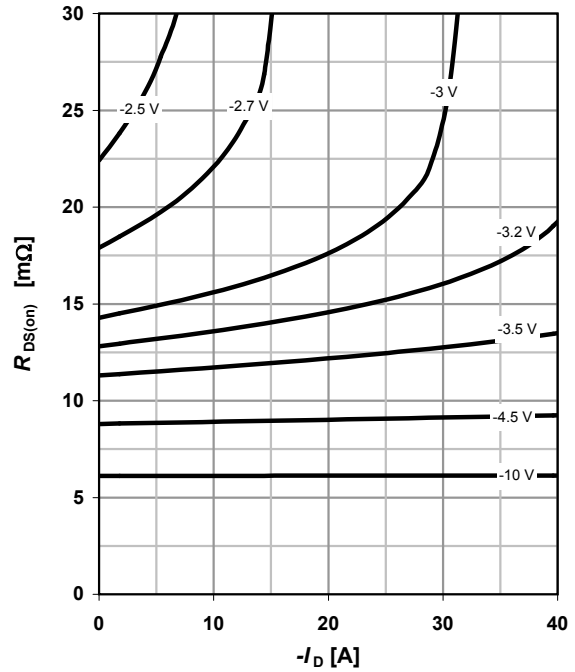
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

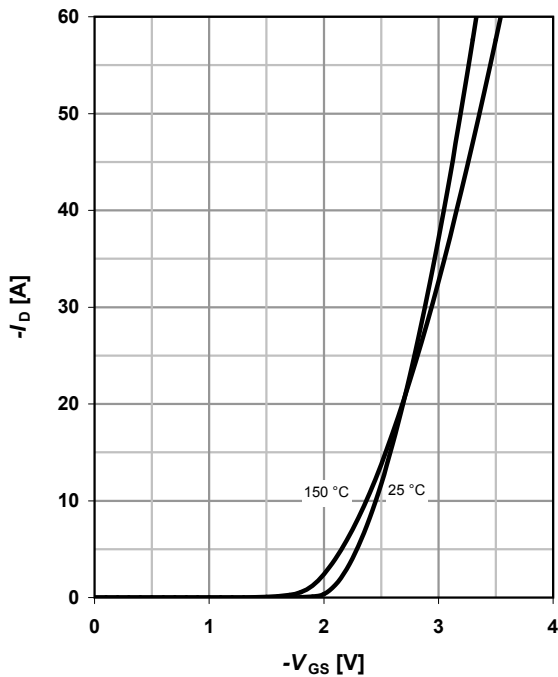
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

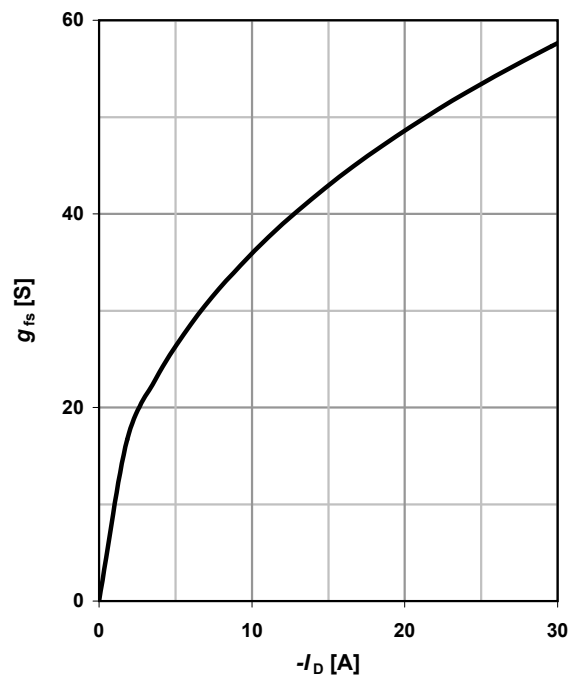
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



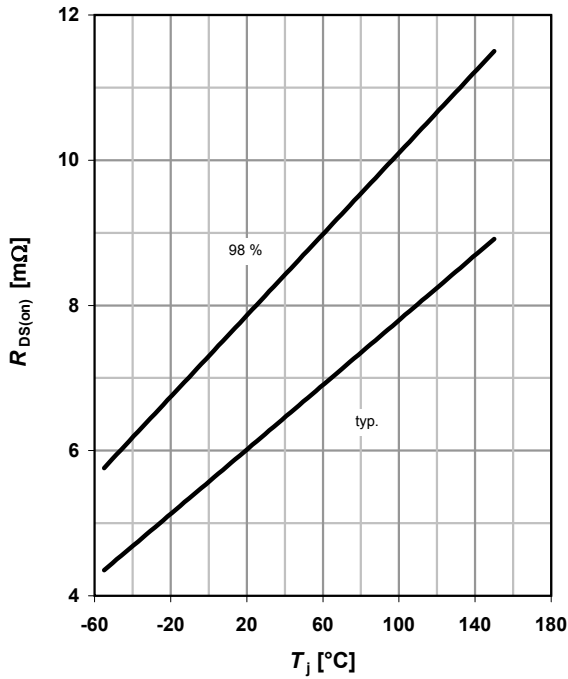
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



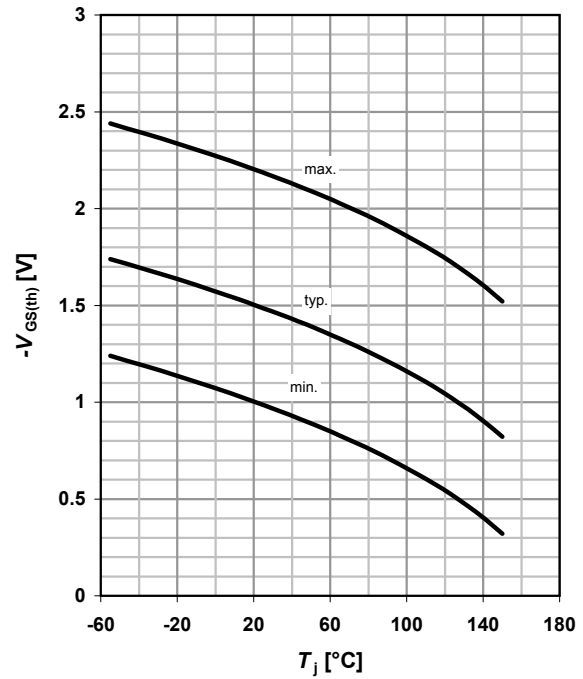
**9 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j); I_D = -30 \text{ A}; V_{GS} = -10 \text{ V}$



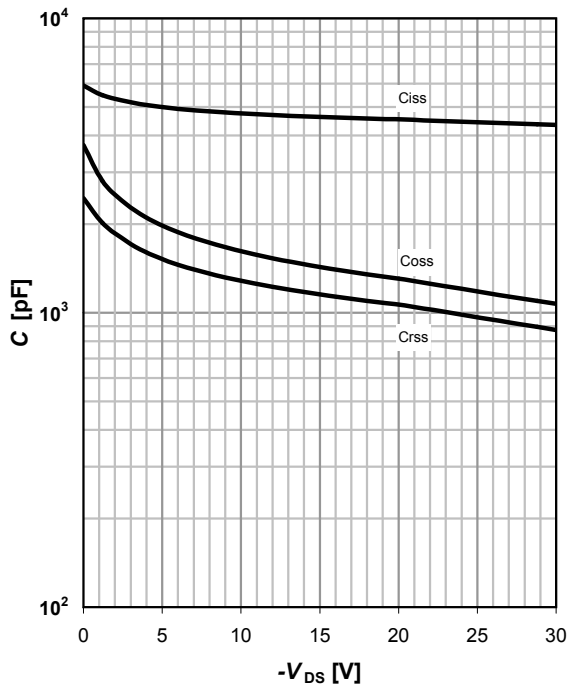
**10 Typ. gate threshold voltage**

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -250 \mu\text{A}$



**11 Typ. capacitances**

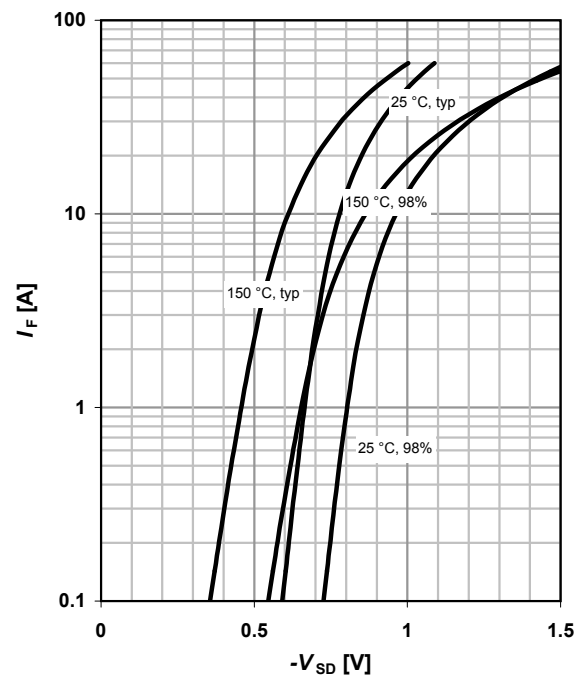
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

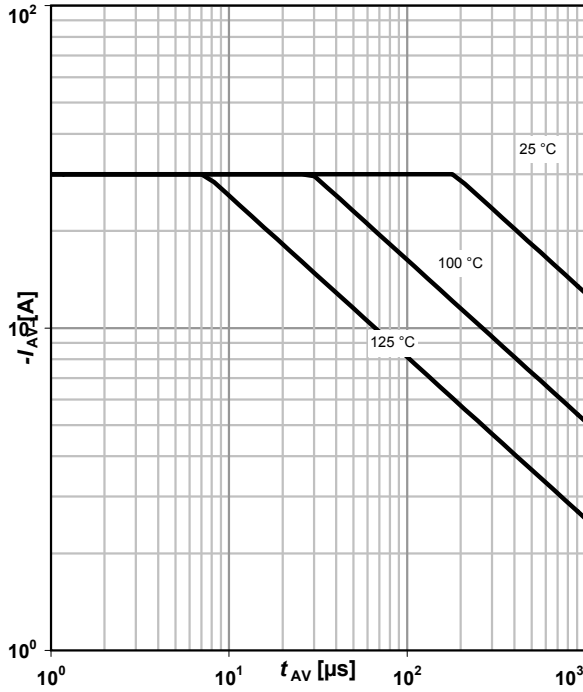
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

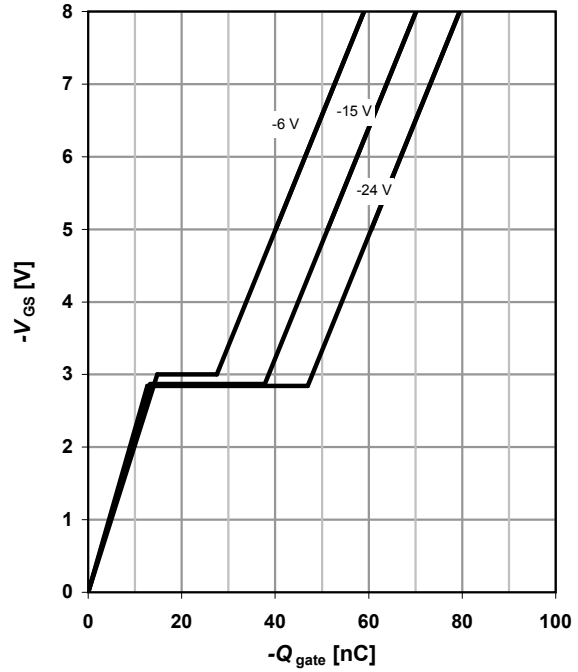
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

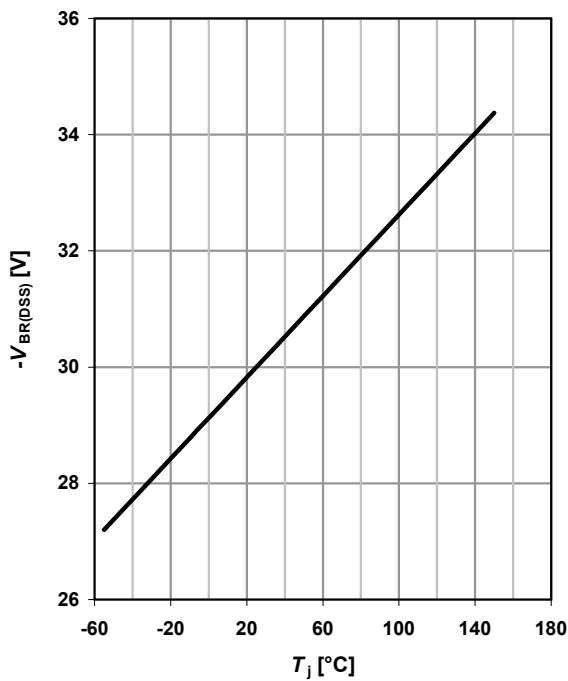
$V_{GS}=f(Q_{gate}); I_D=-30 \text{ A pulsed}$

parameter:  $V_{DD}$

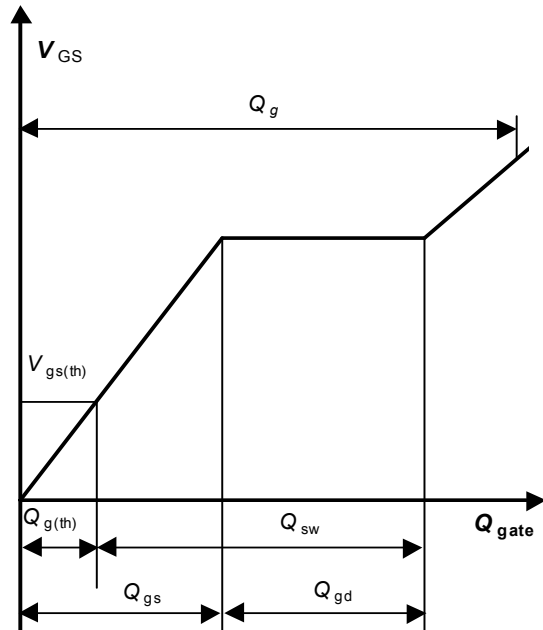


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=-250 \mu\text{A}$

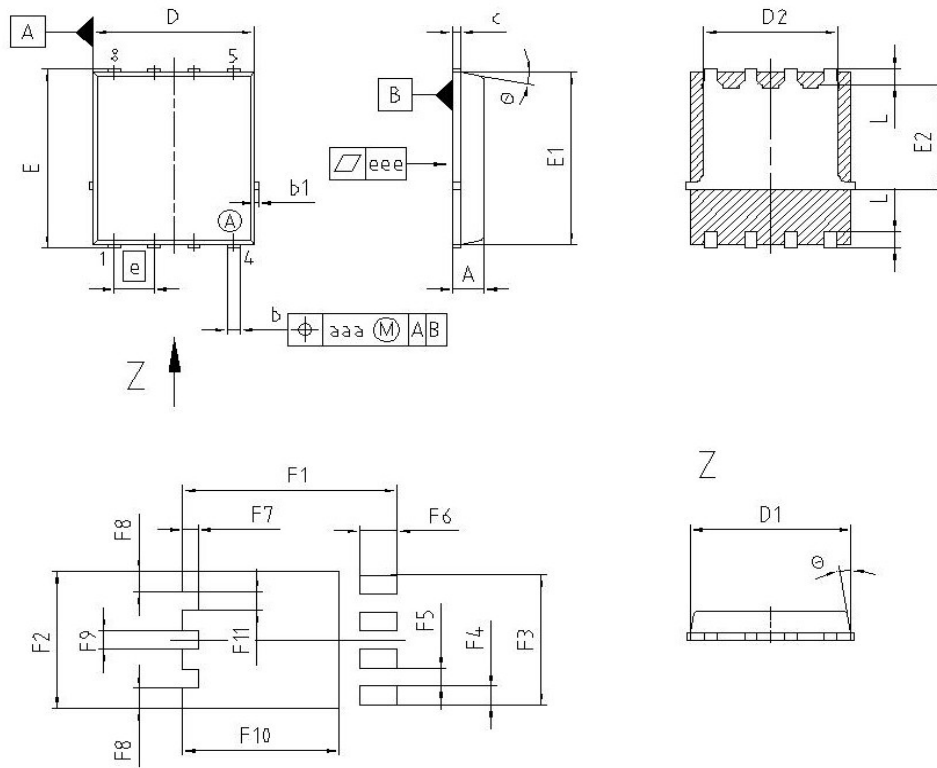


**16 Gate charge waveforms**



Package Outline

PG-TDSON-8: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.100	0.035	0.043
b	0.340	0.540	0.013	0.021
b1	0.000	0.120	0.000	0.005
c	0.150	0.350	0.006	0.014
D=D1	4.950	5.350	0.195	0.211
D2	4.200	4.400	0.165	0.173
E	5.950	6.350	0.234	0.250
E1	5.700	6.100	0.224	0.240
E2	3.400	3.800	0.134	0.150
e	1.270		0.050	
N	8		8	
L	0.450	0.650	0.018	0.026
$\theta$	9°	11°	9°	11°
aaa	0.250		0.010	
eee	0.050		0.002	
F1	6.750	6.950	0.266	0.274
F2	4.600	4.800	0.181	0.189
F3	4.360	4.560	0.172	0.180
F4	0.550	0.750	0.022	0.030
F5	0.520	0.720	0.020	0.028
F6	1.100	1.300	0.043	0.051
F7	0.400	0.600	0.016	0.024
F8	0.600	0.800	0.024	0.031
F9	0.530	0.730	0.021	0.029
F10	4.900	5.100	0.193	0.201
F11	0.535	0.735	0.021	0.029

**REFERENCE**  
JEDEC / MO-240

**SCALE**

**EUROPEAN PROJECTION**

**ISSUE DATE**  
23-08-2006

**FILE**  
TDSON\_1

Dimensions in mm



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
**© 2008 Infineon Technologies AG**  
**All Rights Reserved.**

### **Legal Disclaimer**

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

### **Information**

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

### **Warnings**

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

[www.s-manuals.com](http://www.s-manuals.com)